

1064nm APD module series

SKU :GD6212Y / GD6213Y / GD6219Y

OVERVIEW

The device is a 1064nm enhanced silicon avalanche photodiode module with built-in pre-amplification circuit, which can amplify the weak current signal and convert it into voltage signal output to realize the "light-electricity-signal amplification" conversion process.

FEATURES

Ortho-illuminated planar chip structure

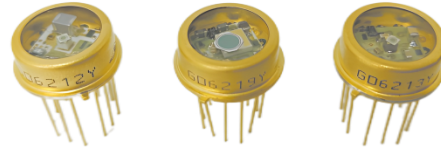
High response frequency

High detector sensitivity

APPLICATION

Laser distance measurement

LIDAR
Laser Warning



OPTICAL CHARACTERISTICS (@Ta=22±3°C)

Model	GD6212Y	GD6213Y	GD6219Y
Package type	TO-8	TO-8	TO-8
Diameter of photosensitive surface(mm)	0.8	0.8	3
Spectral response range(nm)	400~1100	400~1100	400~1100
Breakdown voltage(V)	350~500	350~500	350~500
Responsiveness M=100 I=1064nm(kV/W)	150	200	280
Rise time(ns)	8.8	2	7
Bandwidth(MHz)	40	175	50
Equivalent noise power(pW/√Hz)	0.15	0.15	2.7
Operating voltage temperature coefficient T=-40°C~85°C(V/°C)	2.2	2.2	2.4
Concentricity(μm)	≤50	≤50	≤50
Global alternative models with the same performance	C30950	C30659-1060-R8BH	C30659-1060-3A